IN THE SPECIFICATION

Please enter the following amended paragraphs in the Specification.

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To overcome this, a buffer can be added to the band-gap circuit as is shown in Figure 2. In essence the same circuit as in Figure 1, the circuitry associated with transistors 201 through 207 and resistors 211 and 212 provides the same functionality as the circuitry in Figure 1, thereby providing a band gap reference unit within the larger band gap reference circuit. The current source shown at 214 is implemented in this illustration as a MOSFET current source. PNP transistors 203 and 204 share a common base which is shunted to the collector of transistor 203. NPN transistors 201 and 202 also share a common base that connects to V_{BG}, the band-gap voltage. Transistor 205 has a base connected to the common collectors of transistors 202 and 204. The collector of transistor 205 is connected to the drain of transistor 206 which shares a common gate with transistor 207. The common gate of transistors 206 and 207 is shunted to the drain-collector connection between transistors 205 and 206. In the implementation illustrated in Figure 2, m symbolizes the relationship in current flow between transistor 201 and transistor 202. Because their bases are common, the ratio of current flows is constant. The base-emitter voltage of 201 and 202 differs by the voltage across resistor 211.

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Note that, in this embodiment, device 320 is necessary to pull the voltage back up and prevent saturation of transistors 201 and 202. Device 320 can be implemented, in various embodiments, as a resistor or as a transistor with less than 1 V_{BE}. In the illustration of Figure 3, device 320 is disposed between buffer 309 and the band gap reference unit circuit. It is important to note that transistors 203, 204, and 205 can be implemented as either bipolar transistors or MOS transistors.